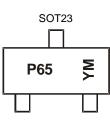


Marking Information



P65 = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: I = 2021) M or \overline{M} = Month (ex: 9 = September)

Date Code Key

Year	2015		2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	С			J	K	L	М	N	0	Р	R	S
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	Vdss	-40	V		
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 5) V_{GS} = -10V	Steady State	T _A = +25°C T _A = +70°C	ID	-2.4 -1.9	А
Continuous Drain Current (Note 6) $V_{GS} = -10V$ State $T_A = +25^{\circ}$ $T_A = +70$			lo	-3.4 -2.7	А
Pulsed Drain Current	I _{DM}	-20	А		

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	PD	0.72	W
Thermal Resistance, Junction to Ambient $@T_A = +25^{\circ}C$ (Note 5)	Reja	171	°C/W
Power Dissipation (Note 6)	PD	1.4	W
Thermal Resistance, Junction to Ambient $@T_A = +25^{\circ}C$ (Note 6)	R _{0JA}	90	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout. 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

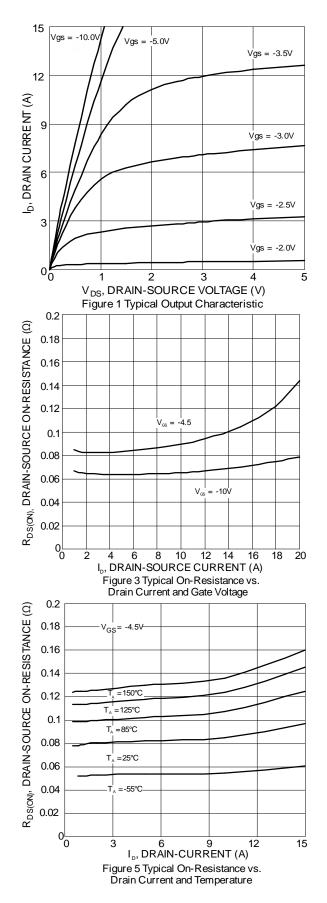


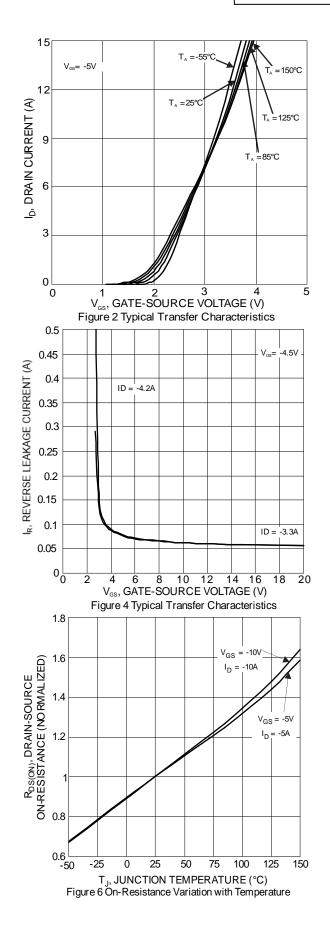
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)						-	
Drain-Source Breakdown Voltage	BVDSS	-40	—	—	V	$V_{GS} = 0V, I_{D} = -250 \mu A$	
Zero Gate Voltage Drain Current TJ = +25°C	IDSS	—	_	-1.0	μA	$V_{DS} = -40V, V_{GS} = 0V$	
Gate-Source Leakage	IGSS	—	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	Vgs(th)	-1.0	—	-3.0	V	$V_{DS} = V_{GS}$, $I_D = -250 \mu A$	
Static Drain-Source On-Resistance	Pro/oni	_	64 85	80	m0	$V_{GS} = -10V, I_{D} = -4.2A$	
Static Drain-Source On-Resistance	Rds(on)			100	mΩ	VGS = -4.5V, ID = -3.3A	
Diode Forward Voltage	V _{SD}	—	-0.7	-1.2	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss		587	—	pF		
Output Capacitance	Coss	—	88	—	pF	Vps = -20V, Vgs = 0V, f = 1.0MHz	
Reverse Transfer Capacitance	Crss	—	40	—	pF		
Gate Resistance	Rg	—	4	—	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge (V _{GS} = -4.5V)	Qg	—	6.1	—	nC		
Total Gate Charge (V _{GS} = -10V)	Qg	—	12.2	—	nC	VDS = -20V, ID = -4.2A	
Gate-Source Charge	Q _{gs}	—	1.8	—	nC		
Gate-Drain Charge	Qgd	—	2.4	—	nC		
Turn-On Delay Time	t _{D(ON)}	_	3.6	—	ns		
Turn-On Rise Time	tR	_	2.9	—	ns	V _{DD} = -15V, V _{GS} = -10V,	
Turn-Off Delay Time	tD(OFF)	_	36.3	—	ns	$I_{D} = -1.0A, R_{G} = 6\Omega$	
Turn-Off Fall Time	tF		15.3	—	ns	7	

7. Short duration pulse test used to minimize self-heating effect.8. Guaranteed by design. Not subject to product testing. Notes:

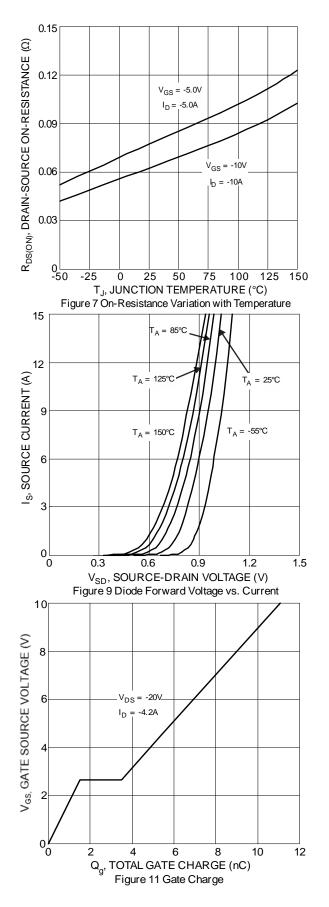


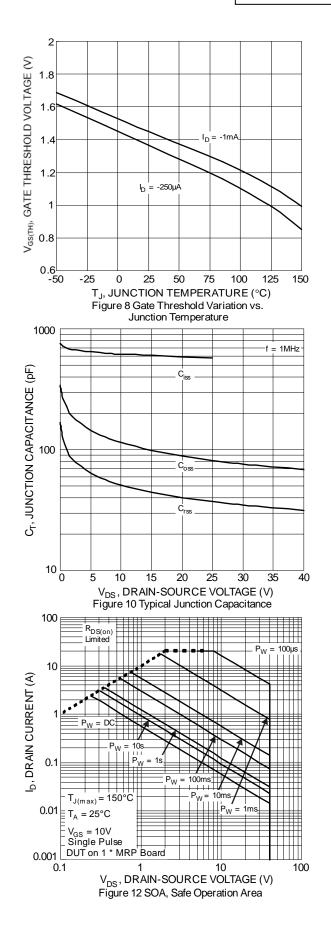




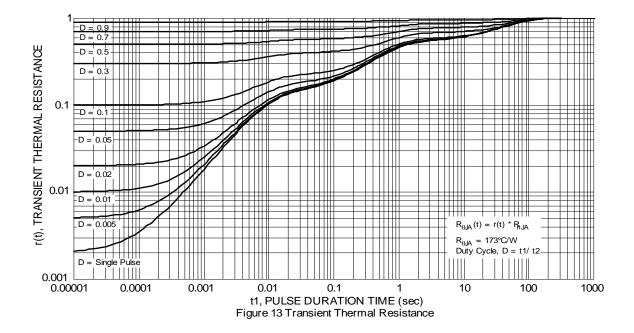
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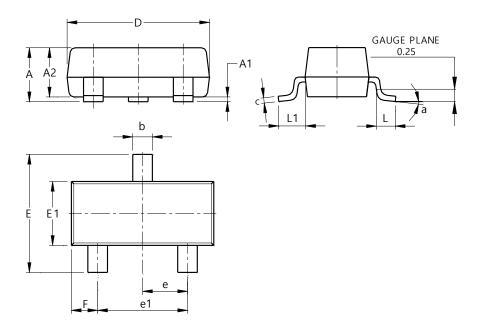






Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

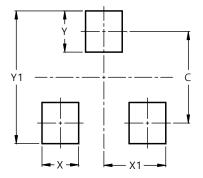


SOT23 (Standard)								
Dim	Min	Max	Тур					
Α	0.90	1.15	1.025					
A1	0.00	0.10	0.05					
A2	0.85	1.10	0.975					
b	0.30	0.51	0.40					
С	0.080	0.202	0.11					
D	2.80	3.00	2.90					
Е	2.25	2.55	2.40					
E1	1.20	1.40	1.30					
е	0.89	1.03	0.915					
e1	1.78	2.05	1.83					
F	0.40	0.60	0.535					
L1	0.45	0.61	0.55					
L	0.25	0.55	0.40					
а	0°	8°						
All Dimensions in mm								

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23 (Standard)



Dimensions	Value (in mm)			
С	2.0			
Х	0.8			
X1	1.35			
Y	0.9			
Y1	2.9			

SOT23 (Standard)



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